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RESEARCH INTERESTS

- ✓ Semiconductor Device Modeling
- ✓ Bandgap Engineered Devices
- ✓ Reliability analysis of advanced heterostructure Devices

Academic Qualifications

Ph. D. (Electronics), Siksha „O" Anusandhan (Deemed to beUniversity), India

M. Tech. (VLSI & Embedded System Design), BPUT, Odisha, India

B.Tech (Electronics&Telecommunication Engineering), BPUT, Odisha, India

Teaching Experience/Industrial Experience/Research Experience

- ✓ Teaching Experience (7 years)
- ✓ Research experience (10 years)

PUBLICATIONS

JOURNALS :

JOURNALARTICLES & CONFERENCE PAPERS

[1]. D. Jena, **Sanghamitra Das**& T. P. Dash, Design and Simulation of Enhancement-Mode Vertical Superjunction GaN HEMT withImproved Ron and Cut-Off Frequency. IETE Journal of Research, pp.1–9, 2023.

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[6]. P. P. Maiti, AjitDash, S.Guhathakurata, **Sanghamitra Das**, Atanu Bag, T. P.Dash, G Ahmad, C K MAITI & S Mallik, Experimental and simulation study of charge transport mechanism in HfTiOx high-k gate dielectric on SiGe heterolayers, Bull Mater Sci, Vol. 45, 2022.
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ANY OTHER

BOOK CHAPTERS

1. **Sanghamitra Das**, Taraprasanna Dash, Biswajit Baral, Sudhansu Mohan Biswal, Devika Jena and Eleena Mohapatra. "Analytical modelling of nanoscale advance devices and their reliability aspects." Nanoelectronics: Physics, Materials and Devices, Elsevier, January 2023, pp.385-408, 10.1016/B978-0-323-91832-9.00011-7, ISBN: 978-0-323-91832-9.
2. **Sanghamitra Das**. "Stress Generation Techniques in CMOS Technology." Stress and Strain Engineering at Nanoscale in Semiconductor Devices, CRC Press, May 2021, www.routledge.com/Stress-and-Strain-Engineering-at-Nanoscale-in-Semiconductor-Devices/Maiti/p/book/9780367519292, ISBN 9780367519292

PATENTS

3. Application Number : 202131048431
   Title of Invention : Monitoring and Control of PV systems connected to the grid with a conventional inverter and with an interlaced inverter.
   Date of publication : 12-11-2021

4. Application Number : 202131050907
   Title of Invention : Monitoring And Evaluating The Operation Of Electronic Noses.
   Date of publication: 10-12-2021